

# RJH60F7BDPQ-A0

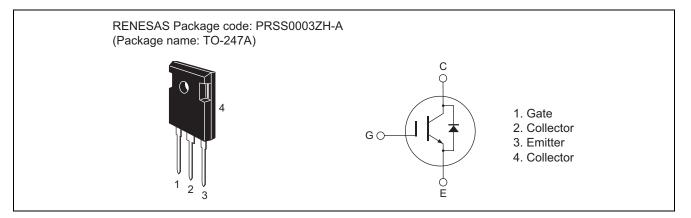
600V - 50A - IGBT High Speed Power Switching

R07DS0677EJ0200 Rev.2.00 Nov 21, 2014

## Features

- Low collector to emitter saturation voltage  $V_{CE(sat)} = 1.35$  V typ. (at  $I_C = 50$  A,  $V_{GE} = 15$  V,  $Tj = 25^{\circ}C$ )
- Built in fast recovery diode in one package
- Trench gate and thin wafer technology
- High speed switching  $t_f = 74$  ns typ. (at  $I_C = 30$  A,  $V_{CE} = 400$  V,  $V_{GE} = 15$  V,  $Rg = 5 \Omega$ ,  $Tj = 25^{\circ}C$ , inductive load)

### Outline



## **Absolute Maximum Ratings**

|   |            |   |             | $(Tc = 25^{\circ}C)$ |
|---|------------|---|-------------|----------------------|
| Item  |            | Symbol                                  | Ratings     | Unit                 |
| Collector to emitter voltage                    |            | V <sub>CES</sub>                        | 600         | V                    |
| Gate to emitter voltage                         |            | V <sub>GES</sub>                        | ±30         | V                    |
| Collector current                               | Tc = 25°C  | lc                                      | 90          | А                    |
|   | Tc = 100°C | lc                                      | 50          | А                    |
| Collector peak current                          |            | ic(peak) Note1                          | 180         | А                    |
| Collector to emitter diode forward peak current |            | i <sub>DF</sub> (peak) <sup>Note2</sup> | 100         | А                    |
| Collector dissipation                           |            | Pc                                      | 328.9       | W                    |
| Junction to case thermal impedance (IGBT)       |            | өј-с                                    | 0.38        | °C/W                 |
| Junction to case thermal impedance (Diode)      |            | θj-cd                                   | 1.1         | °C/W                 |
| Junction temperature                            |            | Tj                                      | 150         | °C                   |
| Storage temperature                             |            | Tstg                                    | -55 to +150 | °C                   |
|   |            | •                                       | •           |                      |

Notes: 1. Pulse width limited by safe operating area.

2.  $PW \leq 5~\mu s,~duty~cycle \leq 1\%$ 



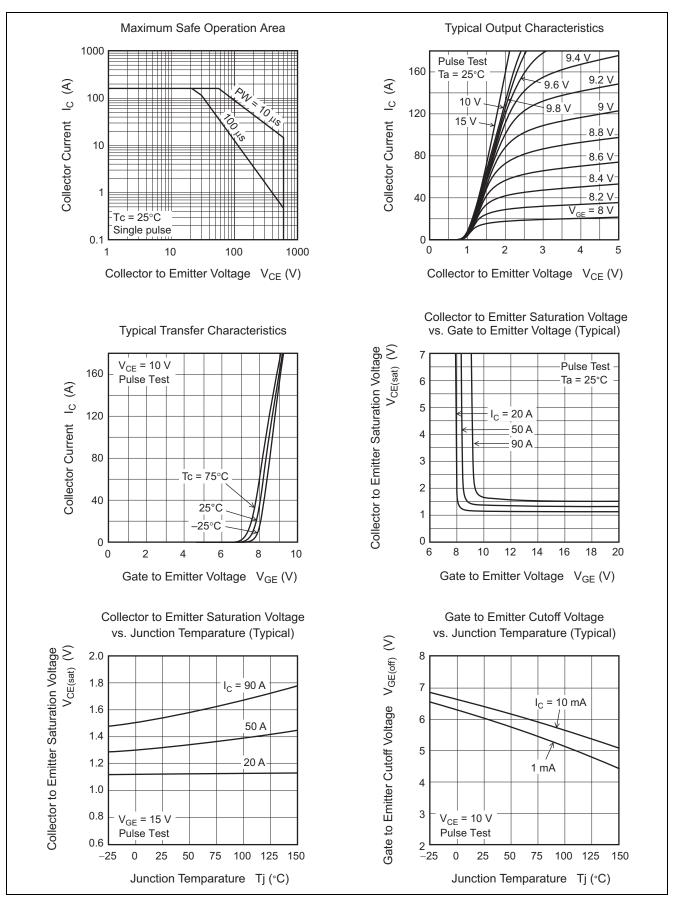
# **Electrical Characteristics**

|   |                      |     |      |      |      | $(Tj = 25^{\circ}C)$  |
|---|----------------------|-----|------|------|------|---|
| Item                                    | Symbol               | Min | Тур  | Max  | Unit | Test Conditions   |
| Zero gate voltage collector current     | I <sub>CES</sub>     | _   |      | 100  | μΑ   | $V_{CE} = 600V, V_{GE} = 0$   |
| Gate to emitter leak current            | I <sub>GES</sub>     | _   |      | ±1   | μΑ   | $V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$   |
| Gate to emitter cutoff voltage          | V <sub>GE(off)</sub> | 4   |      | 8    | V    | $V_{CE} = 10V, I_{C} = 1 \text{ mA}$  |
| Collector to emitter saturation voltage | V <sub>CE(sat)</sub> | _   | 1.35 | 1.75 | V    | $I_{C} = 50 \text{ A}, V_{GE} = 15 \text{V}^{\text{Note3}}$   |
|   | V <sub>CE(sat)</sub> |     | 1.6  |      | V    | $I_{C} = 90 \text{ A}, V_{GE} = 15 V^{Note3}$   |
| Input capacitance                       | Cies                 |     | 4700 |      | pF   | $V_{CE} = 25 V$ $V_{GE} = 0 V$ $f = 1 MHz$  |
| Output capacitance                      | Coes                 |     | 198  |      | pF   |   |
| Reverse transfer capacitance            | Cres                 |     | 83   |      | pF   |   |
| Switching time                          | t <sub>d(on)</sub>   |     | 63   |      | ns   | $\label{eq:CE} \begin{array}{l} I_C = 30 \text{ A}, \\ V_{CE} = 400 \text{ V},  V_{GE} = 15 \text{ V} \\ \text{Rg} = 5 \ \Omega^{\text{ Note3}} \\ \text{Inductive load} \end{array}$ |
|   | tr                   |     | 30   |      | ns   |   |
|   | t <sub>d(off)</sub>  |     | 142  |      | ns   |   |
|   | t <sub>f</sub>       |     | 74   |      | ns   |   |
| C-E diode forward voltage               | V <sub>ECF</sub>     |     | 2.5  | 3.0  | V    | $I_F = 30 \text{ A}^{\text{Note3}}$   |
| C-E diode reverse recovery time         | t <sub>rr</sub>      |     | 25   |      | ns   | I <sub>F</sub> = 30 A   |
|   |                      |     |      |      |      | di <sub>F</sub> /dt = 100 A/µs  |

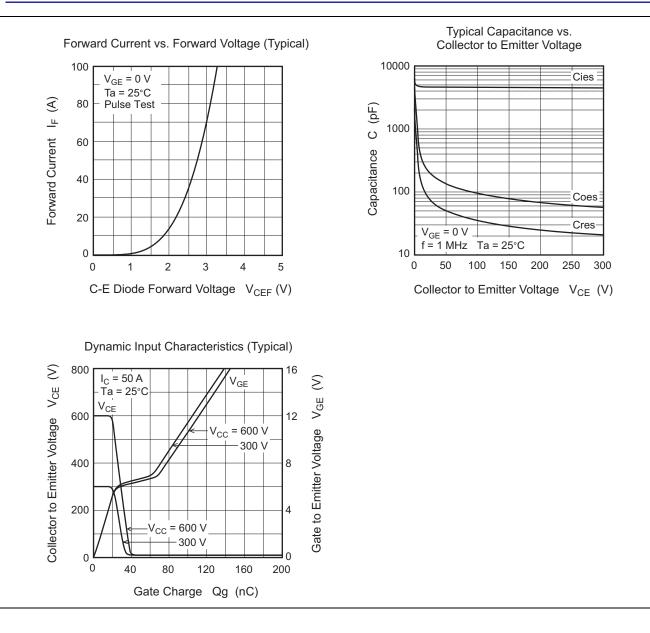
Notes: 3. Pulse test



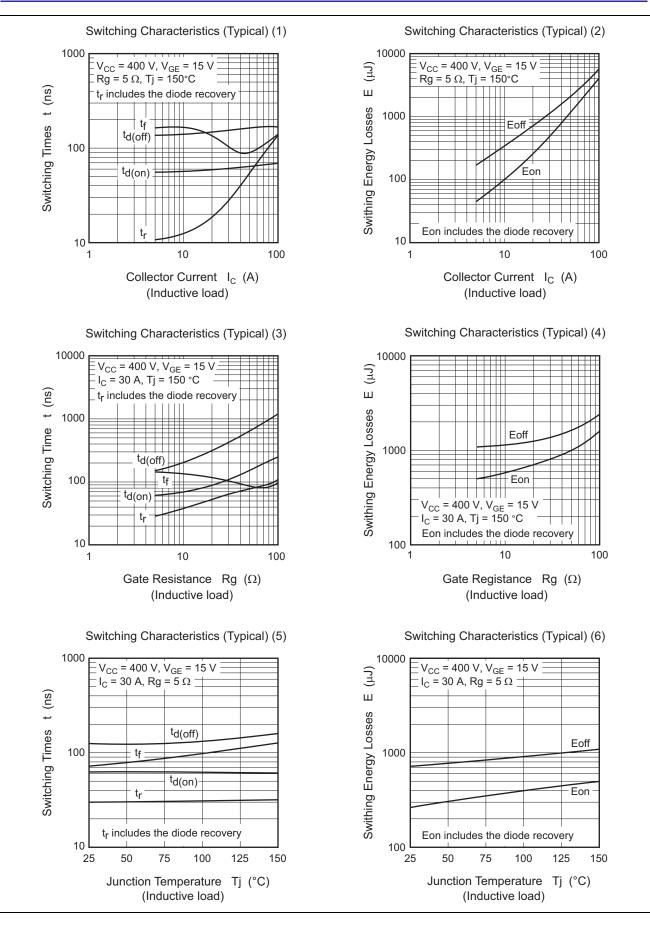
#### **Main Characteristics**



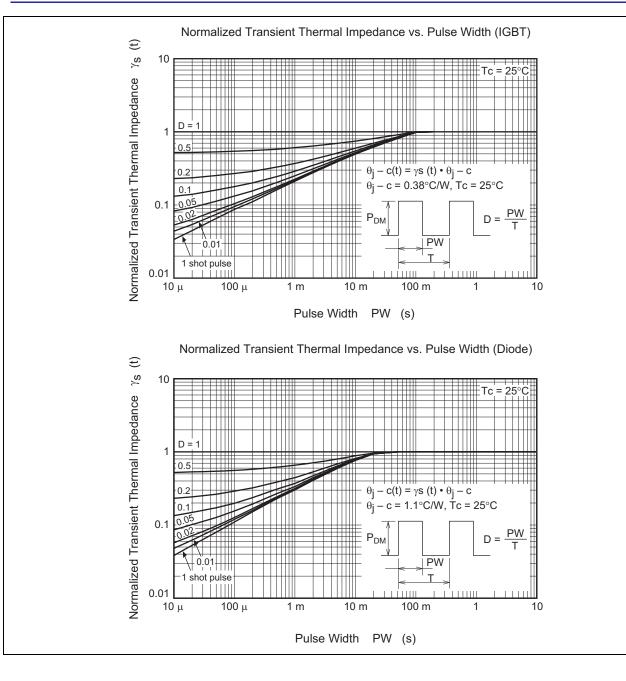




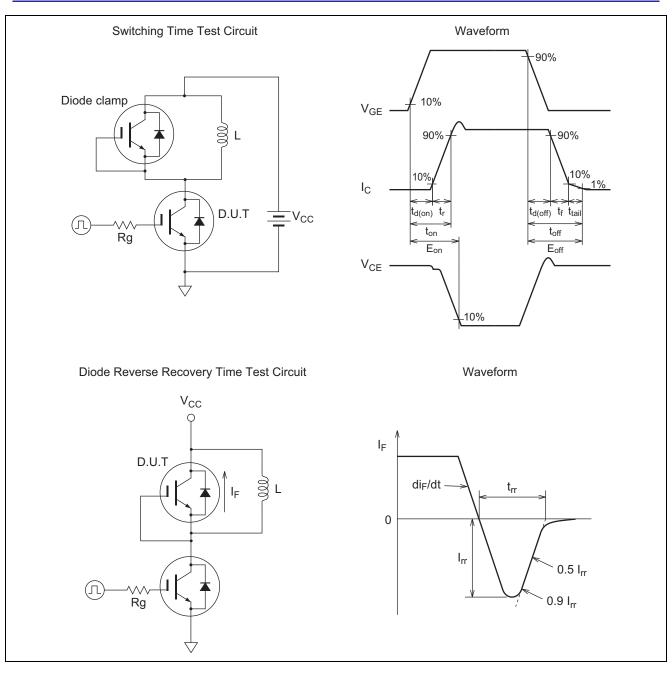






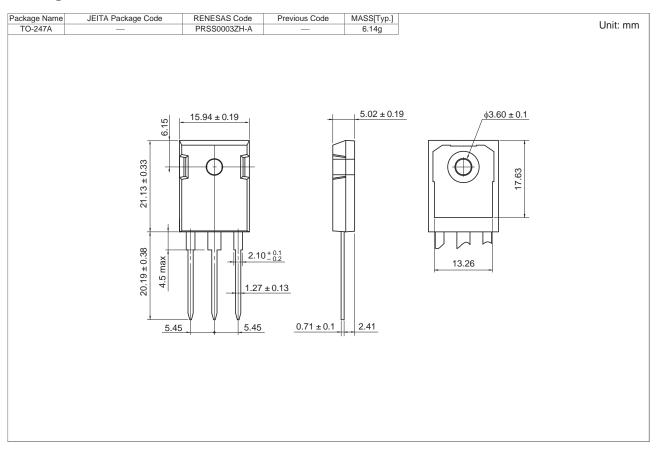








### **Package Dimensions**



## **Ordering Information**

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJH60F7BDPQ-A0#T0     | 240 pcs  | Box (Tube)         |



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